



DV SERIES

6 to 10kV, 55 to 75mA, 75nS
Axial Lead Low Current Diodes



Features

- Subminiature Package
- Molded Plastic Body, ANSI/UL94 V-0 Rated Material

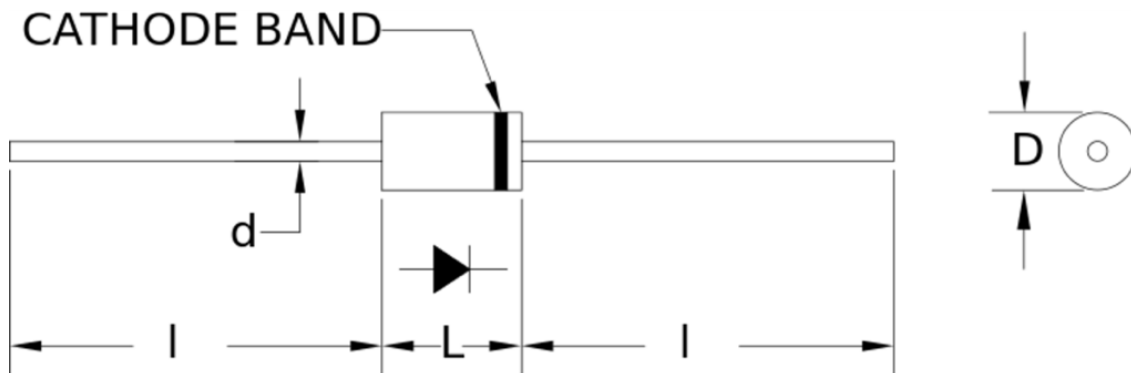
Specifications¹

Part Number	V _{RRM} V	I _{FAVM} mA	V _F V	I _R μA	I _{FSM} A	C _J pF	T _{RR} nS	L in.	D in.	d in.	l in.
DV6P	6000	75	8.0	0.02	3	1.30	75	0.195	0.08	0.02	1.0
DV8P	8000	60	11.5	0.02	3	0.90	75	0.195	0.08	0.02	1.0
DV10P	10000	55	16.0	0.04	3	0.65	75	0.195	0.08	0.02	1.0

Temperature °C	
Operating Temperature	-55 to 150
Storage Temperature	-55 to 175
Maximum Junction Temperature	150

¹25°C ambient temperature unless stated otherwise.

Drawings²

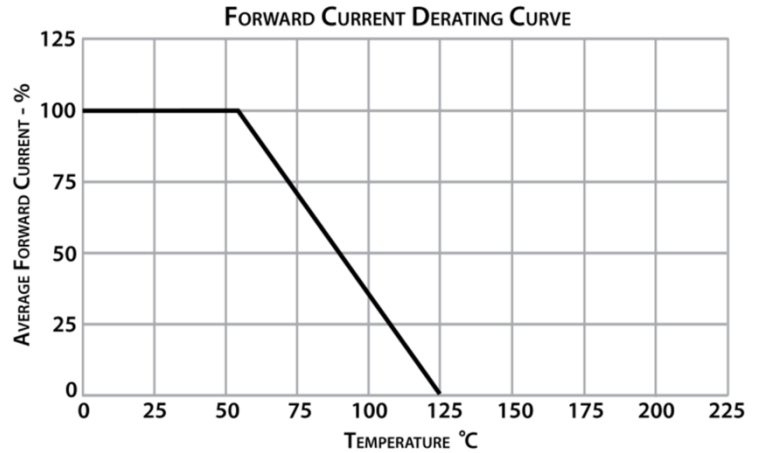
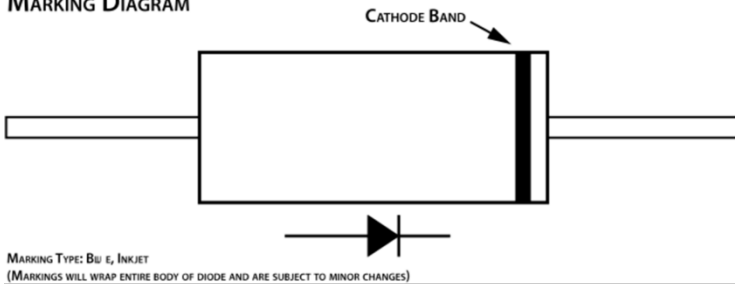


²Dimensions in inches, tolerances ± 0.020 except as noted



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MARKING DIAGRAM



Specification Definitions

Specifications		Conditions
V_RRM	Maximum Repetitive Reverse Voltage	-
I_FAVM	Maximum Average Forward Current	At T _A = 55°C
V_F	Maximum Forward Voltage Drop	At 20mA
I_R	Maximum Leakage Current	At V _{RRM}
I_FSM	Maximum Surge Current	At 8.3mS, Single Half Sine
C_J	Typical Junction Capacitance	At V _R = 0VDC, f = 1MHz
T_{RR}	Maximum Reverse Recovery Time	I _F = 0.5 I _F AVM; I _R = -I _F AVM; I _{RR} = -0.25 I _F AVM

Note: Specifications subject to change without notice. Photo is representation only.

